Batch Coating System

- High Throughput
  [4 Side Coating In One Batch or Equipped with Planetary Rotary Sample Holder]
- Multi Layer Coating
- Double Sided Simultaneous Coating
- Swichable between FCVA ta-c & Metal Sources

System Capabilities:

- FCVA Deposition
- Sputtering Deposition
- Ion Beam Etching / Pre-Cleaning

Batch Coating System

Type of Coatings:

- ta-C
- Metal / Alloys
- Oxides
- Nitrides
- Silicon(Sputtering only)

System Features:

- Rotary Substrate Holder (Single Wafer or Quartet-Wafer Capability)
- Substrate Rotation
- Large Coating Area Up to Ø250mm
- Real Time Process Monitoring
- User-Friendly Interface
- User Defined Coating Recipe
- Data Log for Parameters and Events
- Multi-Source Process Chamber
  - FCVA Source
  - Ion Beam Source (optional)
  - Sputtering Source (optional)
- Dynamic Real Time Compensation
  - Excellent process repeatability

Performance

Parameter	FCVA	Sputtering	Ion Beam
Uniformity Coverage	< ±5% (over Ø250 mm)	±5%	
Repeatability	±10% (normal mode) ±5% (compensation mode)	±5%	
Macro-Particle Level (for ta-C)	< 1/cm^2 (for particles > 1 μm)	NA	
Base Pressure	~ 1 x 10^{-6} torr		
Substrate Rotation Speed	<100 rpm		

Specification

Dimension	3450x 1800 x 2200 mm (LxWxH)
Power Input	3 Phase, 30 kW
Cooling Water	30 l/min @ 0.3 ~ 0.4 MPa (22 °C)
Process Gas	Dry N_2 for venting, Ar for ion beam and sputtering
Pumping System	TP for Process Chamber

Ion Beam Source

Source Type	Kaufman w/ filament neutralizer
Process Gass	Ar or ther inert gases
Ion Beam Energy	300 - 1000eV
Ion Beam Current	50 - 200 mA

Sputter Cathode (optional)

Maximum Sputtering Power	2KW - Pulse DC
Cathode Voltage	100 - 800 V
Discharge Current	1 - 50 A
Working Pressure	~5.0 x 10^{-3} torr

*Specifications and performance provided are subject to changes without prior notice.